

L Number	Hits	Search Text	DB	Time stamp
1	1022	SiC and FET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 13:45
2	0	multples adj alternate adj layers	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 13:46
3	54457	multiple\$1 adj layer\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 13:47
4	94	(SiC and FET) and (multiple\$1 adj layer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 13:52
5	681	stack\$5 adj alternat\$5 adj layer\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 13:53
6	4	(SiC and FET) and (stack\$5 adj alternat\$5 adj layer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 14:19
7	32611	compound adj semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 14:20
8	16	(stack\$5 adj alternat\$5 adj layer\$1) and (compound adj semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 14:56
9	4832723	alternat\$5 adl layer\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 14:57
10	25734	alternat\$5 adj layer\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 15:05
11	18087	compound and GaAs	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 15:06
12	965	(alternat\$5 adj layer\$1) and (compound and GaAs)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 15:07

13	147	((alternat\$5 adj layer\$1) and (compound and GaAs)) and FET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 15:46
14	4	"6654604"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 16:12
15	1		USPAT	2004/06/15 15:47
16	1		USPAT	2004/06/15 15:47
17	1		USPAT	2004/06/15 15:48
18	1		USPAT	2004/06/15 15:48
19	14	"5013685"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 16:14
20	460	delta adj dope\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 16:15
21	0	delta adj dope\$5 adj SiC	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 16:15
22	399	\$2doped adj silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 16:16
23	13	(\$2doped adj silicon adj carbide) and MISFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 16:18
24	36	(\$2doped adj silicon adj carbide) and FET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 16:27
25	417	delta adj doped	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 16:28
26	24	(delta adj doped) and SiC and MOSFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/15 16:28
27	1		USPAT	2004/06/15 16:45
28	1		USPAT	2004/06/15 16:47
29	1		USPAT	2004/06/15 16:48